New Jersey Semi-Conductor Products, Inc.

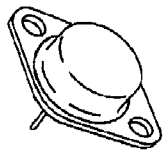
20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

2N6767/2N6768
N-Channel Power MOSFETs, 15 A, 350 V/400 V

Description
These devices are n-channel, enhancement mode, power MOSFETs designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

- **V_{GS} Rated at ±20 V**
- **Silicon Gate for Fast Switching Speeds**
- **I_{DSS}, $R_{DS(on)}$ Specified at Elevated Temperature**
- **Rugged**
- **Low Drive Requirements**
- **Ease of Paralleling**



2N6767
2N6768

Maximum Ratings

Symbol	Characteristic	Rating 2N6768	Rating 2N6767	Unit
V_{DSS}	Drain to Source Voltage	400	350	V
V_{DGR}	Drain to Gate Voltage R_{GS} = 1.0 MΩ	400	350	V
V_{GS}	Gate to Source Voltage	±20	±20	V
T_J, T_{stg}	Operating Junction and Storage Temperatures	−55 to +150	−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/16" From Case for 10 s	300	300	°C
Maximum On-State Characteristics				
$R_{DS(on)}$	Static Drain-to-Source On Resistance	0.3	0.4	Ω
I_D	Drain Current Continuous at T_C = 25°C Continuous at T_C = 100°C	 14 9.0	 12 7.75	A
I_{DM}	Pulsed	25[2]	20[2]	
Maximum Thermal Characteristics				
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.83	0.83	°C/W
P_D	Total Power Dissipation at T_C = 25°C at T_C = 100°C	 150 60	 1.50 60	W
	Linear Derating Factor	1.2	1.2	W/°C

Notes
All values are JEDEC registered except as noted. For information concerning connection diagram and package outline, refer to Section 7.

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit	Test Conditions
Off Characteristics					
$V_{(BR)DSS}$	Drain Source Breakdown Voltage[1]			V	V_{GS} = 0 V, I_D = 1.0 mA
	2N6768	400[2]			
	2N6767	350[2]			
I_{DSS}	Zero Gate Voltage Drain Current		1	mA	V_{DS} = Rated V_{DSS}, V_{GS} = 0 V
			4		V_{DS} = Rated V_{DSS}, V_{GS} = 0 V, T_C = 125°C
I_{GSS}	Gate-Body Leakage Current		±100	nA	V_{GS} = ±20 V, V_{DS} = 0 V
On Characteristics					
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	I_D = 1 mA, V_{DS} = V_{GS}
$R_{DS(on)}$	Static Drain-Source On-Resistance			Ω	V_{GS} = 10 V
	2N6768		0.3		I_D = 9.0 A
	2N6767		0.4		I_D = 7.75 A
	2N6768		0.66		I_D = 9.0 A
	2N6767		0.88		I_D = 7.75 A
$V_{DS(on)}$	Drain-Source On-Voltage			V	V_{GS} = 10 V
	2N6768		5.6		I_D = 14 A
	2N6767		5.4		I_D = 12 A
g_{fs}	Forward Transconductance	8.0	24	S (℧)	V_{DS} = 15 V, I_D = 9.0 A
Dynamic Characteristics					
C_{iss}	Input Capacitance	1000	3000	pF	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz
C_{oss}	Output Capacitance	200	600	pF	
C_{rss}	Reverse Transfer Capacitance	50	200	pF	
Switching Characteristics (T_C = 25°C, *Figures 9, 10*)					
$t_{d(on)}$	Turn-On Delay Time		35	ns	V_{DD} = 180 V, I_D = 9.0 A, V_{GS} = 10 V, R_{GEN} = 4.7 Ω, R_{GS} = 4.7 Ω
t_r	Rise Time		65	ns	
$t_{d(off)}$	Turn-Off Delay Time		150	ns	
t_f	Fall Time		75	ns	
Q_g	Total Gate Charge		120[2]	nC	V_{GS} = 10 V, I_D = 16 A, V_{DD} = 400 V

Electrical Characteristics (Cont.) (T_C = 25°C unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit	Test Conditions
Source-Drain Diode Characteristics						
I_S	Continuous Source Current				A	
	2N6768			14		
	2N6767			12		
I_{SM}	Pulsed Source Current				A	
	2N6768			25[2]		
	2N6767			20[2]		
V_{SD}	Diode Forward Voltage				V	V_{GS} = 0 V
	2N6768	0.85		1.7		I_S = 14 A
	2N6767	0.8		1.6		I_S = 12 A
t_{rr}	Reverse Recovery Time		1000[2]		ns	V_{GS} = 0 V, T_J = 150°C, I_F = I_{SM}, dI_F/dt = 100 A/μs
Q_{RR}	Reverse Recovery Charge		25[2]		μC	V_{GS} = 0 V, T_J = 150°C, I_F = I_{SM}, dI_F/dt = 100 A/μs